





FEATURES

Converts +5V Logic Supply to ±5V	System
Wide Input Voltage Range	1.5V to 10V
Efficient Voltage Conversion	99.9%
Excellent Power Efficiency	98%
Low Power Supply	80μΑ @ 5V _{IN}
Low Cost and Easy to Use	·
- Only Two External Capacitors R	equired

- RS232 Negative Power Supply
- Available in Small Outline (SO) Package
- Improved ESD Protection Up to 3kV
- No Dx Diode Required for High Voltage Operation

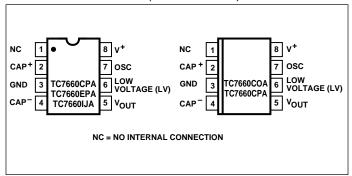
GENERAL DESCRIPTION

The TC7660 is a pin-compatible replacement for the Industry standard TC7660 charge pump voltage converter. It converts a +1.5V to +10V input to a corresponding – 1.5V to -10V output using only two low-cost capacitors, eliminating inductors and their associated cost, size and EMI.

The on-board oscillator operates at a nominal frequency of 10kHz. Operation below 10kHz (for lower supply current applications) is possible by connecting an external capacitor from OSC to ground (with pin 1 open).

The TC7660 is available in both 8-pin DIP and 8-pin SOIC packages in commercial and extended temperature ranges.

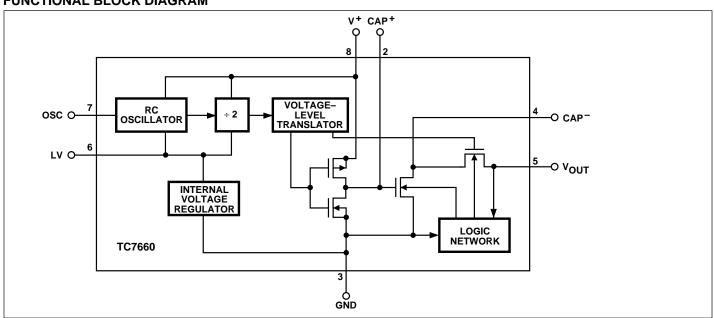
PIN CONFIGURATION (DIP and SOIC)



ORDERING INFORMATION

Part No.	Package	Temperature Range			
TC7660COA	8-Pin SOIC	0°C to +70°C			
TC7660CPA	8-Pin Plastic DIP	0°C to +70°C			
TC7660EOA	8-Pin SOIC	− 40°C to +85°C			
TC7660EPA	8-Pin Plastic DIP	− 40°C to +85°C			
TC7660IJA	8-Pin CerDIP	− 40°C to +85°C			
TC7660MJA	8-Pin CerDIP	– 55°C to +125°C			
TC7660EV	Evaluation Kit for	Evaluation Kit for			
	Charge Pump Far	Charge Pump Family			

FUNCTIONAL BLOCK DIAGRAM



TC7660

ABSOLUTE MAXIMUM RATINGS*

Supply Voltage+10.5V LV and OSC Inputs
Voltage (Note 1) – 0.3V to (V++0.3V)
for $V^+ < 5.5V$
$(V^+ - 5.5V)$ to $(V^+ + 0.3V)$
for $V^+ > 5.5V$
Current Into LV (Note 1)
Output Short Duration (V _{SUPPLY} ≤ 5.5V) Continuous
Power Dissipation ($T_A \le 70^{\circ}$ C) (Note 2)
CerDIP800mW
Plastic DIP730mW
SOIC470mW

Operating Temperature Range

C Suffix	0°C to +70°C
I Suffix	– 25°C to +85°C
E Suffix	40°C to +85°C
M Suffix	– 55°C to +125°C
Storage Temperature Range	
Lead Temperature (Soldering, 10) sec)+300°C

*Static-sensitive device. Unused devices must be stored in conductive material. Protect devices from static discharge and static fields. Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions above those indicated in the operation sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

ELECTRICAL CHARACTERISTICS: Specifications Measured Over Operating Temperature Range With,

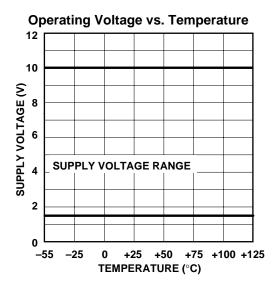
Specifications Measured Over Operating Temperature Range With, $V^+ = 5V$, $C_{OSC} = 0$, Test Circuit (Figure 1), unless otherwise indicated.

Symbol	Parameter	Test Conditions	Min	Тур	Max	Unit
l+	Supply Current	R _L = ∞	_	80	180	μΑ
V ⁺ H	Supply Voltage Range, High	$\begin{aligned} &\text{Min} \leq T_A \leq \text{Max}, \\ &R_L = 10 \text{ k}\Omega, \text{ LV Open} \end{aligned}$	3	_	10	V
V ⁺ L	Supply Voltage Range, Low	$\begin{aligned} &\text{Min} \leq T_A \leq \text{Max}, \\ &R_L = 10 \text{ k}\Omega, \text{ LV to GND} \end{aligned}$	1.5	_	3.5	V
R _{OUT}	Output Source Resistance	I _{OUT} = 20mA, T _A = 25°C	_	70	100	Ω
		$I_{OUT} = 20$ mA, 0 °C $\leq T_A \leq +70$ °C (C Device)	_	_	120	Ω
		$I_{OUT} = 20$ mA, -40 °C $\leq T_A \leq +85$ °C (I Device)	_	_	130	Ω
		$I_{OUT} = 20$ mA, -55 °C $\leq T_A \leq +125$ °C (M Device)	-	104	150	Ω
		V^+ = 2V, I_{OUT} = 3 mA, LV to GND 0°C \leq T _A \leq +70°C	_	150	300	Ω
		$V^{+} = 2V$, $I_{OUT} = 3$ mA, LV to GND $-55^{\circ}C \le T_{A} \le +125^{\circ}C$ (Note 3)	_	160	600	Ω
Fosc	Oscillator Frequency	Pin 7 open	_	10	_	kHz
P _{EFF}	Power Efficiency	$R_L = 5k\Omega$	95	98	_	%
V _{OUT} E _{FF}	Voltage Conversion Efficiency	R _L = ∞	97	99.9	_	%
Zosc	Oscillator Impedance	V+ = 2V		1	_	MΩ
		$V^{+} = 5V$		100	_	kΩ

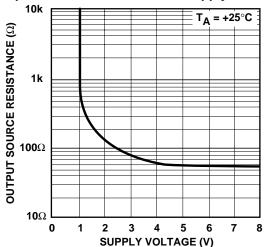
NOTES: 1. Connecting any input terminal to voltages greater than V⁺ or less than GND may cause destructive latch-up. It is recommended that no inputs from sources operating from external supplies be applied prior to "power up" of the TC7660.

- 2. Derate linearly above 50°C by 5.5 mW/°C.
- 3. TC7660M only.
- 4. The TC7660 can be operated without the Dx diode over full temperature and voltage range.

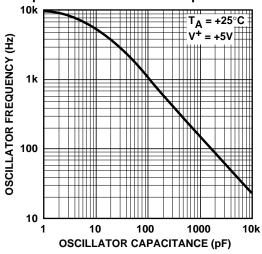
TYPICAL PERFORMANCE CHARACTERISTICS (Circuit of Figure 1)

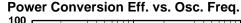


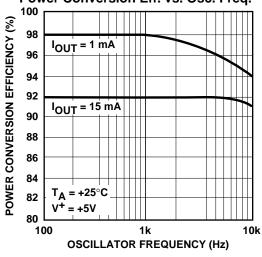
Output Source Resistance vs. Supply Voltage



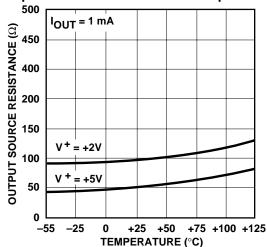
Freq. of Osc. vs. Ext. Osc. Capacitance



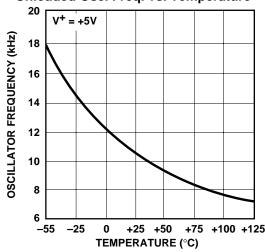




Output Source Resistance vs. Temperature

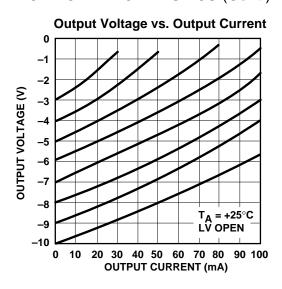


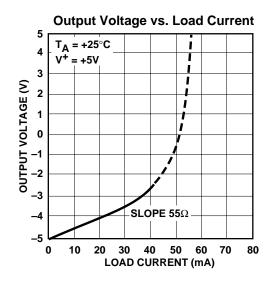
Unloaded Osc. Freq. vs. Temperature



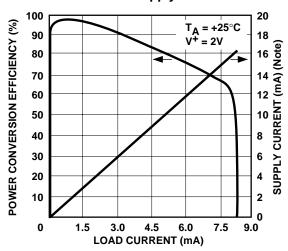
TC7660

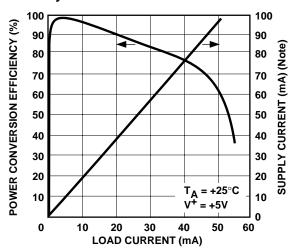
TYPICAL CHARACTERISTICS (Cont.)



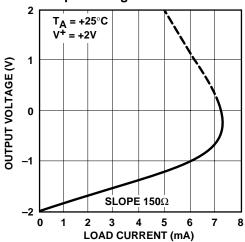


Supply Current and Power Conversion Efficiency vs. Load Current





Output Voltage vs. Load Current



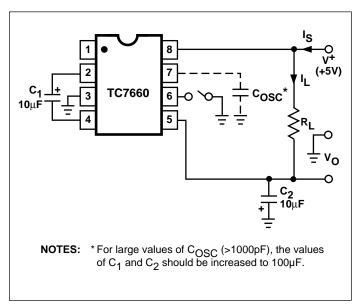


Figure 1. TC7660 Test Circuit

Detailed Description

The TC7660 contains all the necessary circuitry to implement a voltage inverter, with the exception of two external capacitors, which may be inexpensive 10 μF polarized electrolytic capacitors. Operation is best understood by considering Figure 2, which shows an idealized voltage inverter. Capacitor C_1 is charged to a voltage, V+, for the half cycle when switches S_1 and S_3 are closed. (**Note:** Switches S_2 and S_4 are open during this half cycle.) During the second half cycle of operation, switches S_2 and S_4 are closed, with S_1 and S_3 open, thereby shifting capacitor C_1 negatively by V+ volts. Charge is then transferred from C_1 to C_2 , such that the voltage on C_2 is exactly V+, assuming ideal switches and no load on C_2 .

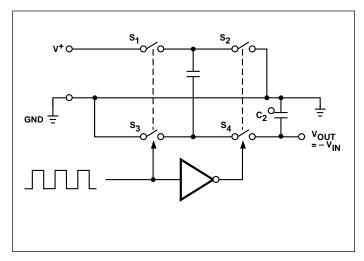


Figure 2. Idealized Charge Pump Inverter

The four switches in Figure 2 are MOS power switches; S_1 is a P-channel device, and S_2 , S_3 and S_4 are N-channel devices. The main difficulty with this approach is that in integrating the switches, the substrates of S_3 and S_4 must always remain reverse-biased with respect to their sources, but not so much as to degrade their ON resistances. In addition, at circuit start-up, and under output short circuit conditions ($V_{OUT} = V^+$), the output voltage must be sensed and the substrate bias adjusted accordingly. Failure to accomplish this will result in high power losses and probable device latch-up.

This problem is eliminated in the TC7660 by a logic network which senses the output voltage (V_{OUT}) together with the level translators, and switches the substrates of S_3 and S_4 to the correct level to maintain necessary reverse bias.

The voltage regulator portion of the TC7660 is an integral part of the anti-latch-up circuitry. Its inherent voltage drop can, however, degrade operation at low voltages. To improve low-voltage operation, the LV pin should be connected to GND, disabling the regulator. For supply voltages greater than 3.5V, the LV terminal must be left open to ensure latch-up-proof operation and prevent device damage.

Theoretical Power Efficiency Considerations

In theory, a capacitive charge pump can approach 100% efficiency if certain conditions are met:

- (1) The drive circuitry consumes minimal power.
- (2) The output switches have extremely low ON resistance and virtually no offset.
- (3) The impedances of the pump and reservoir capacitors are negligible at the pump frequency.

TC7660

The TC7660 approaches these conditions for negative voltage multiplication if large values of C_1 and C_2 are used. **Energy is lost only in the transfer of charge between capacitors if a change in voltage occurs.** The energy lost is defined by:

$$E = 1/2 C_1 (V_1^2 - V_2^2)$$

 V_1 and V_2 are the voltages on C_1 during the pump and transfer cycles. If the impedances of C_1 and C_2 are relatively high at the pump frequency (refer to Figure 2), compared to the value of R_L , there will be a substantial difference in voltages V_1 and V_2 . Therefore, it is not only desirable to make C_2 as large as possible to eliminate output voltage ripple, but also to employ a correspondingly large value for C_1 in order to achieve maximum efficiency of operation.

Dos and Don'ts

- Do not exceed maximum supply voltages.
- Do not connect LV terminal to GND for supply voltages greater than 3.5V.
- Do not short circuit the output to V⁺ supply for voltages above 5.5V for extended periods; however, transient conditions including start-up are okay.
- When using polarized capacitors in the inverting mode, the + terminal of C₁ must be connected to pin 2 of the TC7660 and the + terminal of C₂ must be connected to GND Pin 3.

Simple Negative Voltage Converter

Figure 3 shows typical connections to provide a negative supply where a positive supply is available. A similar scheme may be employed for supply voltages anywhere in the operating range of +1.5V to +10V, keeping in mind that pin 6 (LV) is tied to the supply negative (GND) only for supply voltages below 3.5V.

The output characteristics of the circuit in Figure 3 are those of a nearly ideal voltage source in series with 70Ω . Thus, for a load current of -10mA and a supply voltage of +5V, the output voltage would be -4.3V.

The dynamic output impedance of the TC7660 is due, primarily, to capacitive reactance of the charge transfer capacitor (C_1). Since this capacitor is connected to the output for only 1/2 of the cycle, the equation is:

$$X_C = \frac{2}{2\pi f C_1} = 3.18\Omega,$$

where f = 10kHz and $C_1 = 10\mu F$.

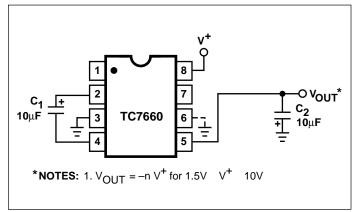


Figure 3. Simple Negative Converter

Paralleling Devices

Any number of TC7660 voltage converters may be paralleled to reduce output resistance (Figure 4). The reservoir capacitor, C_2 , serves all devices, while each device requires its own pump capacitor, C_1 . The resultant output resistance would be approximately:

$$R_{OUT} = \frac{R_{OUT} \text{ (of TC7660)}}{\text{n (number of devices)}}$$

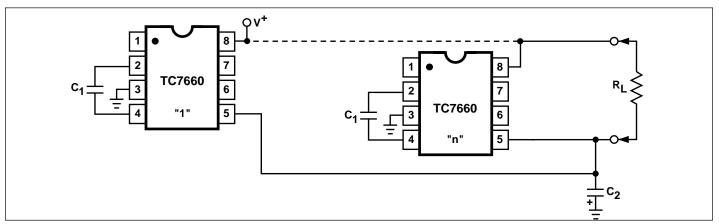


Figure 4. Paralleling Devices Lowers Output Impedance

Cascading Devices

The TC7660 may be cascaded as shown (Figure 6) to produce larger negative multiplication of the initial supply voltage. However, due to the finite efficiency of each device, the practical limit is 10 devices for light loads. The output voltage is defined by:

$$V_{OUT} = -n (V_{IN})$$

where n is an integer representing the number of devices cascaded. The resulting output resistance would be approximately the weighted sum of the individual TC7660 R_{OUT} values.

Changing the TC7660 Oscillator Frequency

It may be desirable in some applications (due to noise or other considerations) to increase the oscillator frequency. This is achieved by overdriving the oscillator from an external clock, as shown in Figure 6. In order to prevent possible device latch-up, a $1k\Omega$ resistor must be used in series with the clock output. In a situation where the designer has generated the external clock frequency using TTL logic, the addition of a $10k\Omega$ pull-up resistor to V⁺ supply is required. Note that the pump frequency with external clocking, as with internal clocking, will be 1/2 of the clock frequency. Output transitions occur on the positive-going edge of the clock.

It is also possible to increase the conversion efficiency of the TC7660 at low load levels by lowering the oscillator frequency. This reduces the switching losses, and is achieved by connecting an additional capacitor, C_{OSC} , as shown in Figure 7. Lowering the oscillator frequency will cause an undesirable increase in the impedance of the pump (C_1) and the reservoir (C_2) capacitors. To overcome this, increase the values of C_1 and C_2 by the same factor that the frequency has been reduced. For example, the addition of a 100pF capacitor between pin 7 (OSC) and pin 8 (V+) will lower the oscillator frequency to 1kHz from its nominal frequency of 10kHz (a multiple of 10), and necessitate a corresponding increase in the values of C_1 and C_2 (from $10\mu F$ to $100\mu F$).

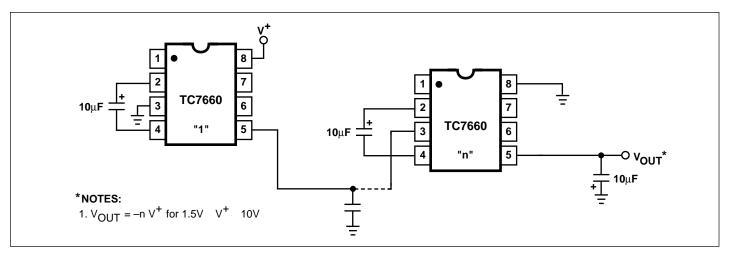


Figure 5. Increased Output Voltage by Cascading Devices

TC7660

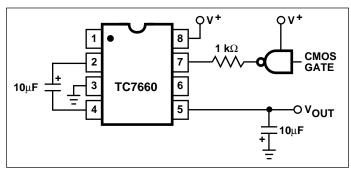


Figure 6. External Clocking

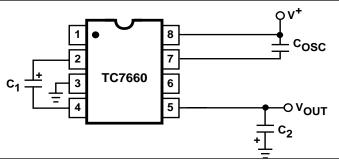


Figure 7. Lowering Oscillator Frequency

Positive Voltage Multiplication

The TC7660 may be employed to achieve positive voltage multiplication using the circuit shown in Figure 8. In this application, the pump inverter switches of the TC7660 are used to charge C_1 to a voltage level of V^+ – V_F (where V^+ is the supply voltage and V_F is the forward voltage drop of diode D_1). On the transfer cycle, the voltage on C_1 plus the supply voltage (V^+) is applied through diode D_2 to capacitor C_2 . The voltage thus created on C_2 becomes ($2 V^+$) – ($2 V_F$), or twice the supply voltage minus the combined forward voltage drops of diodes D_1 and D_2 .

The source impedance of the output (V_{OUT}) will depend on the output current, but for $V^+ = 5V$ and an output current of 10 mA, it will be approximately 60Ω .

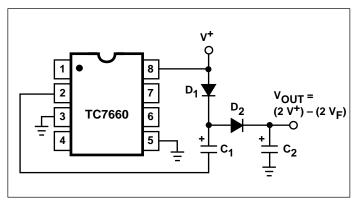


Figure 8. Positive Voltage Multiplier

Combined Negative Voltage Conversion and Positive Supply Multiplication

Figure 9 combines the functions shown in Figures 3 and 8 to provide negative voltage conversion and positive voltage multiplication simultaneously. This approach would be, for example, suitable for generating +9V and – 5V from an existing +5V supply. In this instance, capacitors C_1 and C_3 perform the pump and reservoir functions, respectively, for the generation of the negative voltage, while capacitors C_2 and C_4 are pump and reservoir, respectively, for the multiplied positive voltage. There is a penalty in this configuration which combines both functions, however, in that the source impedances of the generated supplies will be somewhat higher due to the finite impedance of the common charge pump driver at pin 2 of the device.

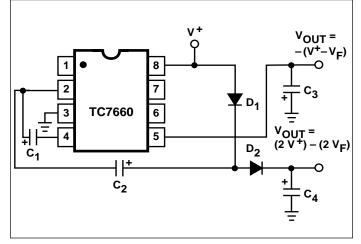


Figure 9. Combined Negative Converter and Positive Multiplier

Efficient Positive Voltage Multiplication/Conversion

Since the switches that allow the charge pumping operation are bidirectional, the charge transfer can be performed backwards as easily as forwards. Figure 10 shows a TC7660 transforming – 5V to +5V (or +5V to +10V, etc.). The only problem here is that the internal clock and switch-drive section will not operate until some positive voltage has been generated. An initial inefficient pump, as shown in Figure 9, could be used to start this circuit up, after which it will bypass the other (D₁ and D₂ in Figure 9 would never turn on), or else the diode and resistor shown dotted in Figure 10 can be used to "force" the internal regulator on.

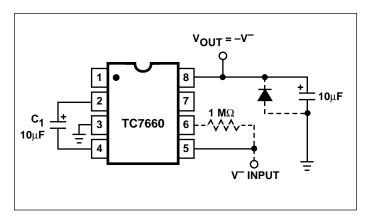


Figure 10. Positive Voltage Conversion

Voltage Splitting

The same bidirectional characteristics used in Figure 10 can also be used to split a higher supply in half, as shown in Figure 11. The combined load will be evenly shared between the two sides. Once again, a high value resistor to the LV pin ensures start-up. Because the switches share the load in parallel, the output impedance is much lower than in the standard circuits, and higher currents can be drawn from the device. By using this circuit, and then the circuit of Figure 5, +15V can be converted (via +7.5V and –7.5V) to a nominal – 15V, though with rather high series resistance (~250 Ω).

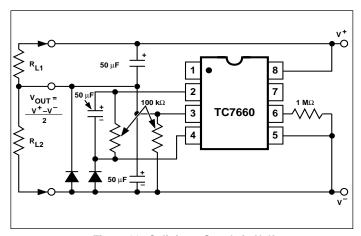
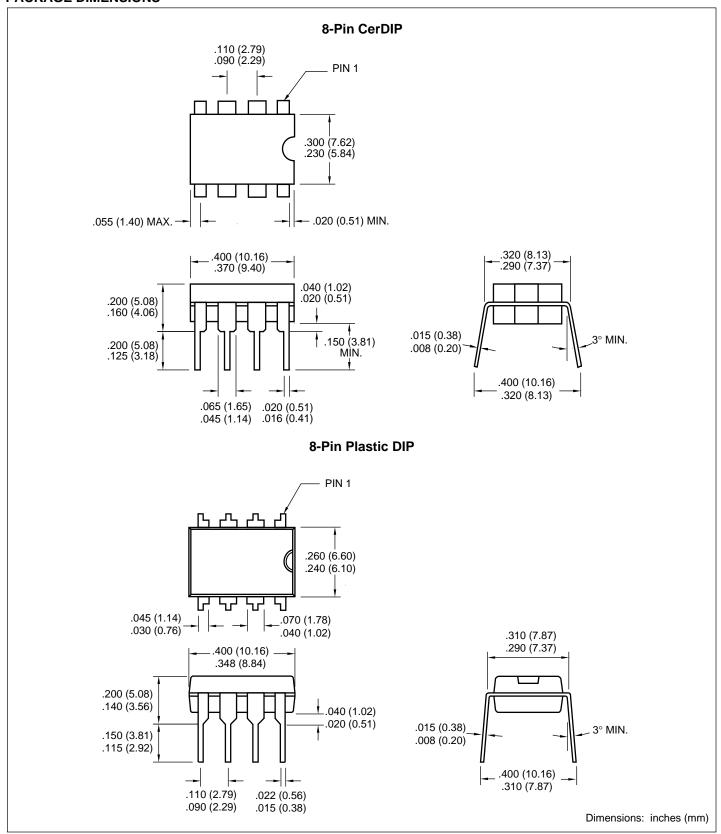


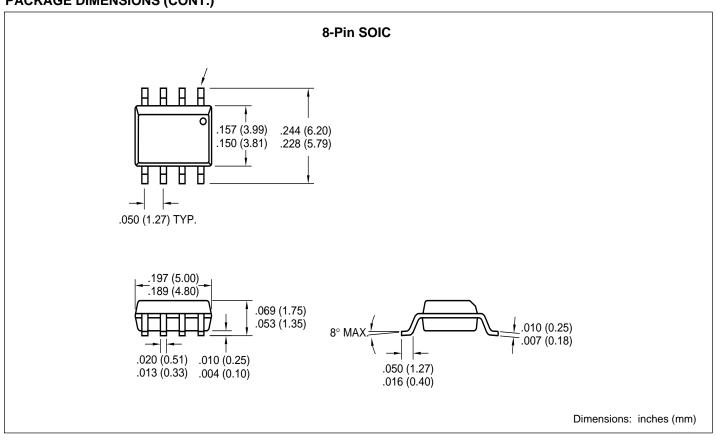
Figure 11. Splitting a Supply in Half

TC7660

PACKAGE DIMENSIONS



PACKAGE DIMENSIONS (CONT.)





WORLDWIDE SALES AND SERVICE

AMERICAS

Corporate Office

2355 West Chandler Blvd.
Chandler, AZ 85224-6199
Tel: 480-792-7200 Fax: 480-792-7277
Technical Support: 480-792-7627
Web Address: http://www.microchip.com

Rocky Mountain

2355 West Chandler Blvd. Chandler, AZ 85224-6199 Tel: 480-792-7966 Fax: 480-792-7456

Atlanta

500 Sugar Mill Road, Suite 200B Atlanta, GA 30350 Tel: 770-640-0034 Fax: 770-640-0307

Austin

Analog Product Sales 8303 MoPac Expressway North Suite A-201 Austin, TX 78759 Tel: 512-345-2030 Fax: 512-345-6085

2 Lan Drive, Suite 120 Westford, MA 01886 Tel: 978-692-3848 Fax: 978-692-3821

Boston

Analog Product Sales Unit A-8-1 Millbrook Tarry Condominium 97 Lowell Road Concord, MA 01742 Tel: 978-371-6400 Fax: 978-371-0050

Chicago

333 Pierce Road, Suite 180 Itasca, IL 60143 Tel: 630-285-0071 Fax: 630-285-0075

Dallas

4570 Westgrove Drive, Suite 160 Addison, TX 75001 Tel: 972-818-7423 Fax: 972-818-2924

Dayton

Two Prestige Place, Suite 130 Miamisburg, OH 45342 Tel: 937-291-1654 Fax: 937-291-9175

Detroit

Tri-Atria Office Building 32255 Northwestern Highway, Suite 190 Farmington Hills, MI 48334 Tel: 248-538-2250 Fax: 248-538-2260

Los Angeles

18201 Von Karman, Suite 1090 Irvine, CA 92612 Tel: 949-263-1888 Fax: 949-263-1338

Mountain View

Analog Product Sales 1300 Terra Bella Avenue Mountain View, CA 94043-1836 Tel: 650-968-9241 Fax: 650-967-1590 **New York**

150 Motor Parkway, Suite 202 Hauppauge, NY 11788 Tel: 631-273-5305 Fax: 631-273-5335

San Jose

Microchip Technology Inc. 2107 North First Street, Suite 590 San Jose, CA 95131 Tel: 408-436-7950 Fax: 408-436-7955

Toronto

6285 Northam Drive, Suite 108 Mississauga, Ontario L4V 1X5, Canada Tel: 905-673-0699 Fax: 905-673-6509

ASIA/PACIFIC

China - Beijing

Microchip Technology Beijing Office New China Hong Kong Manhattan Bldg. No. 6 Chaoyangmen Beidajie Beijing, 100027, No. China Tel: 86-10-85282100 Fax: 86-10-85282104

China - Shanghai

Microchip Technology Shanghai Office Room 701, Bldg. B Far East International Plaza No. 317 Xian Xia Road Shanghai, 200051 Tel: 86-21-6275-5700 Fax: 86-21-6275-5060

Hong Kong

Microchip Asia Pacific RM 2101, Tower 2, Metroplaza 223 Hing Fong Road Kwai Fong, N.T., Hong Kong Tel: 852-2401-1200 Fax: 852-2401-3431

Microchip Technology Inc. India Liaison Office Divyasree Chambers 1 Floor, Wing A (A3/A4) No. 11, OiShaugnessey Road Bangalore, 560 025, India Tel: 91-80-2290061 Fax: 91-80-2290062

Japan

Microchip Technology Intl. Inc. Benex S-1 6F 3-18-20, Shinyokohama Kohoku-Ku, Yokohama-shi Kanagawa, 222-0033, Japan Tel: 81-45-471- 6166 Fax: 81-45-471-6122

Korea

Microchip Technology Korea 168-1, Youngbo Bldg. 3 Floor Samsung-Dong, Kangnam-Ku Seoul, Korea Tel: 82-2-554-7200 Fax: 82-2-558-5934 ASIA/PACIFIC (continued)

Singapore Microchip Technology Singapore Pte Ltd. 200 Middle Road #07-02 Prime Centre Singapore, 188980 Tel: 65-334-8870 Fax: 65-334-8850

Taiwan

Microchip Technology Taiwan 11F-3, No. 207 Tung Hua North Road Taipei, 105, Taiwan Tel: 886-2-2717-7175 Fax: 886-2-2545-0139

EUROPE

Australia

Microchip Technology Australia Pty Ltd Suite 22, 41 Rawson Street Epping 2121, NSW Australia Tel: 61-2-9868-6733 Fax: 61-2-9868-6755

Denmark

Microchip Technology Denmark ApS Regus Business Centre Lautrup hoj 1-3 Ballerup DK-2750 Denmark Tel: 45 4420 9895 Fax: 45 4420 9910

Arizona Microchip Technology SARL Parc díActivite du Moulin de Massy 43 Rue du Saule Trapu Batiment A - Ier Etage 91300 Massy, France Tel: 33-1-69-53-63-20 Fax: 33-1-69-30-90-79

Germany

Arizona Microchip Technology GmbH Gustav-Heinemann Ring 125 D-81739 Munich, Germany Tel: 49-89-627-144 0 Fax: 49-89-627-144-44

Germany

Analog Product Sales Lochhamer Strasse 13 D-82152 Martinsried, Germany Tel: 49-89-895650-0 Fax: 49-89-895650-22

Italy

Arizona Microchip Technology SRL Centro Direzionale Colleoni Palazzo Taurus 1 V. Le Colleoni 1 20041 Agrate Brianza Milan, Italy Tel: 39-039-65791-1 Fax: 39-039-6899883

United Kingdom

Arizona Microchip Technology Ltd. 505 Eskdale Road Winnersh Triangle Wokingham Berkshire, England RG41 5TU Tel: 44 118 921 5869 Fax: 44-118 921-5820

All rights reserved. © 2001 Microchip Technology Incorporated. Printed in the USA. 1/01



Information contained in this publication regarding device applications and the like is intended through suggestion only and may be superseded by updates. It is your responsibility to ensure that your application meets with your specifications. No representation or warranty is given and no liability is assumed by Microchip Technology Incorporated with respect to the accuracy or use of such information, or infringement of patents or other intellectual property rights arising from such use or otherwise. Use of Microchipis products as critical components in life support systems is not authorized except with express written approval by Microchip. No licenses are conveyed, implicitly or otherwise, except as maybe explicitly expressed herein, under any intellectual property rights. The Microchip logo and name are registered trademarks of Microchip Technology Inc. in the U.S.A. and other countries. All rights reserved. All other trademarks mentioned herein are the property of their respective companies.

12 © 2001 Microchip Technology Inc. DS21465A TC7660-7 9/30/96

This datasheet has been downloaded from:

www. Data sheet Catalog.com

Datasheets for electronic components.